

1 Introduction

This document describes the power architecture of the i.MXRT600 and shows all the internal loads of the part and how to control them. It also provides guidance on typical 25C currents based on bench measurements but is not intended to replace the data sheet.

2 Power rails and distribution

The figure below shows a high-level diagram with some of the power domains in the i.MX RT600.

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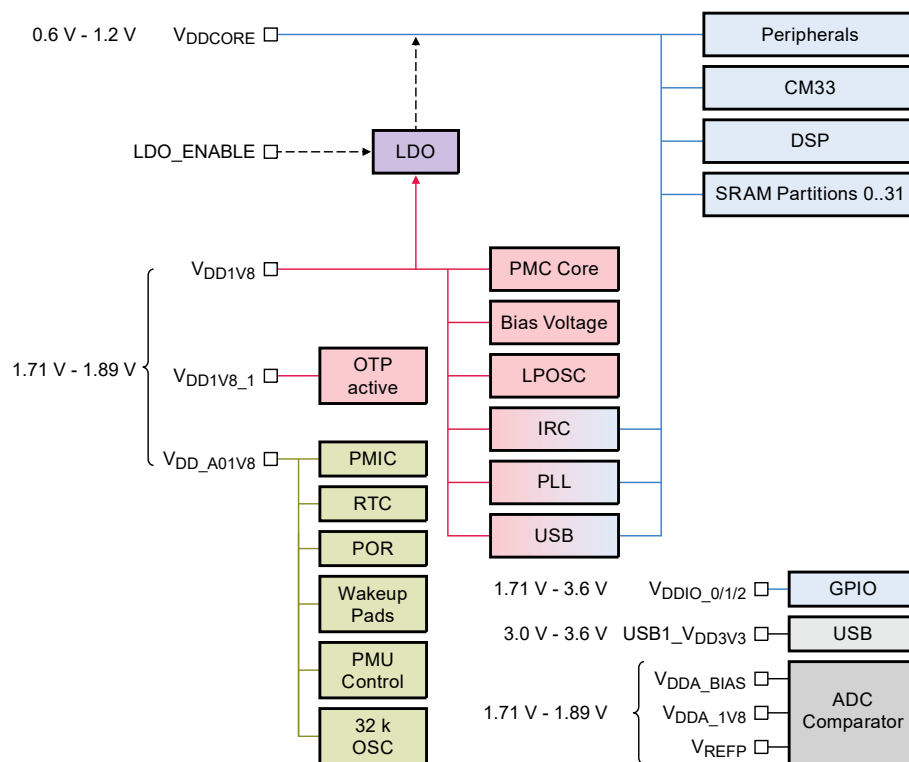
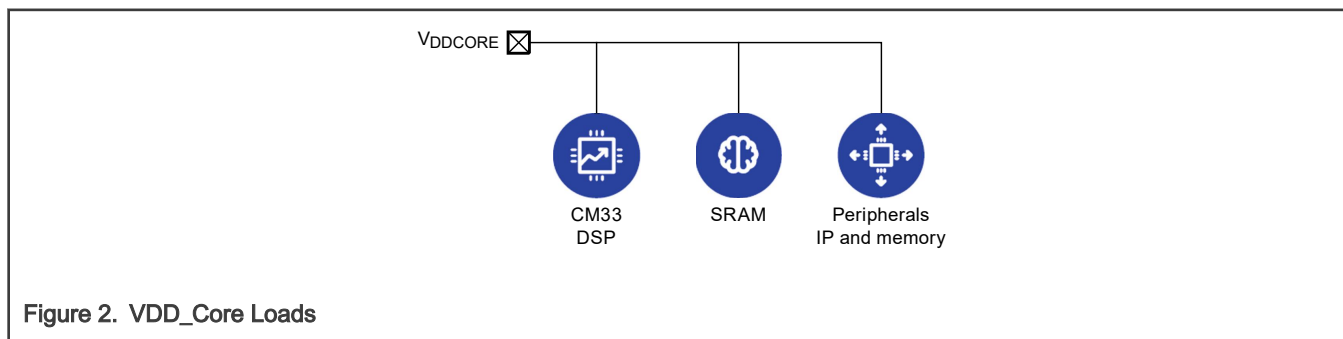


Figure 1. Power Domains

2.1 VDD_Core

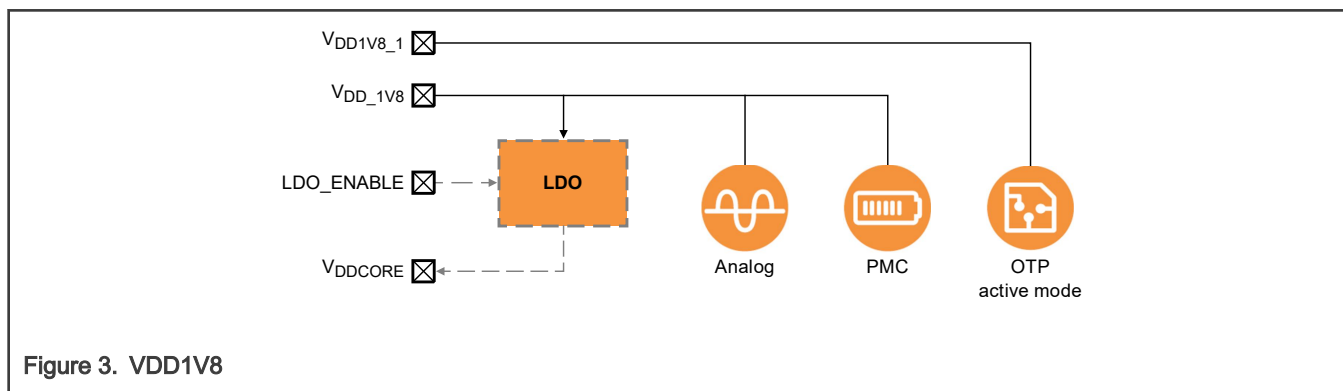


VDD_Core is an adjustable voltage from 0.7 V to 1.155 V. The minimum VDD_Core voltage level in active mode gets determined by the core frequency, as shown in Table 1. For SDK version 2.8 and before (SDK Power Library version = 0x020200): The maximum frequency for the specified VDDCORE voltage is the frequency of the main clock. This is before the CPU CLOCK Divider. The VDDCORE voltage has to be set according to the chosen main clock frequency. For SDK version 2.8.3 and after (SDK Power Library version = 0x02030): The maximum frequency for the specified VDDCORE voltage is the frequency of the clock after CPU CLOCK and DSP clock Divider.

Table 1. VDD_Core minimum voltage in Active mode

| Frequency | min V _{DD_Core} |
|-----------|--------------------------|
| 65 MHz | 0.7 V |
| 140 MHz | 0.8 V |
| 210 MHz | 0.9 V |
| 275 MHz | 1.0 V |
| 300 MHz | 1.13 V |

2.2 VDD1V8



2.2.1 VDD1V8

1.8 V voltage supply is used for on-chip analog functions other than the ADC and comparator. It is also a power supply to the Power Management Core. That includes band gap, POR, temperature sensor, core low-voltage, and high-voltage detection. In addition, it powers the Low-power oscillator, the slow, and fast IRC and the PLL.

2.2.2 VDD1V8_1

1.8 V supply voltage is used for OTP during active mode. In deep-sleep mode, this pin can be powered off to conserve additional current (~ 65 uA). `VDD1V8_1` must be stable before performing any OTP-related functions.

2.2.3 VDD_AO1V8

Supply 1.8 V is used for “always on” features. It includes `RTC`, `RESETN`, `LDO_ENABLE`, `PMIC_IRQ_N`, `PMIC_MODE0`, and `PMIC_MODE1`.

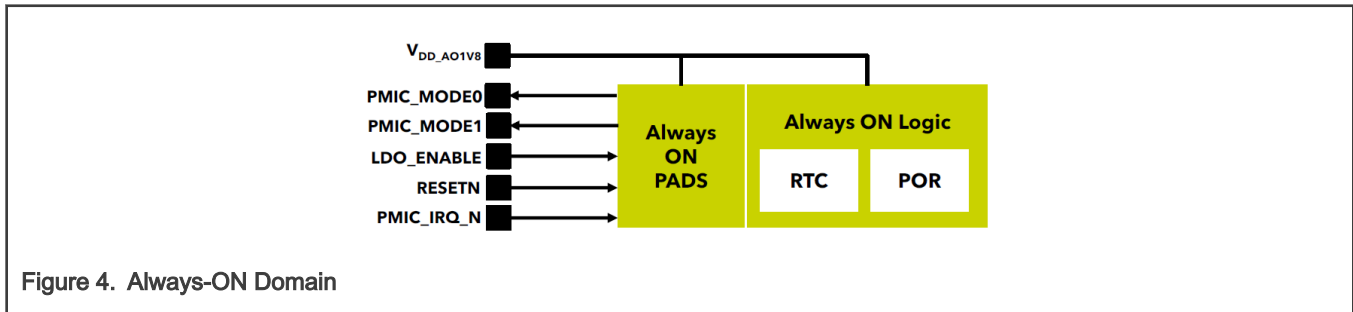


Figure 4. Always-ON Domain

2.2.4 VDDA_1V8

1.8 V analog supply voltage is used for ADC and comparator.

2.2.5 LDO_ENABLE

The `LDO_ENABLE` pin is used to select whether V_{DDCore} is powered using the internal LDO or an external source. When the `LDO_ENABLE` pin is pulled high, V_{DDCore} is supplied from the internal LDO and the LDO is powered from the `VDD1V8`. When the `LDO_ENABLE` pin is pulled low, V_{DDCore} is supplied from an external source.

2.3 VDDIO

This section gives the details of VDDIO.

2.3.1 VDDIO_0/1/2

Supply voltage for GPIO pins. `VDDIO_0`, `VDDIO_1`, and `VDDIO_2` may be supplied at different voltage levels as needed by the application.

2.4 VDD_BIAS

`VDD_BIAS` is a bias for ADC and comparator. `VDD_BIAS` must be equal to the highest VDDIO rail voltage used for the ADC input channel or comparator inputs.

3 Power modes

i.MXRT600 module implements five basic power modes: Active, Sleep, Deep Sleep, Deep Power-down, and Full Deep Power-down. The following sections explain the difference between power modes, using the following de-coding bullets.

↑ ON

→ Software selection ON, OFF, or Low Power

↓ OFF

3.1 Active

The device is in active mode after RESET and the default power configuration is determined by the boot values of the `PDRUNCFG` and `PSCCTL` registers.

↑ CPU, Enabled Memories, and Peripherals.

3.1.1 Active mode (dynamic) power consumption

The following sections show typical bench power data for the core and DSP domains.

3.1.2 Core domain dynamic power

Table 2. Core dynamic current

| Conditions DSP OFF enhanced while (1) code executed from SRAM; Internal LDO disabled | $I_{DDVDDCore}$ |
|---|-----------------|
| CCLK = 12 MHz $V_{DDCore} = 0.7\text{ V}$ | 3.0 mA |
| CCLK = 48 MHz $V_{DDCore} = 0.7\text{ V}$ | 6.0 mA |
| CCLK = 60 MHz $V_{DDCore} = 0.7\text{ V}$ | 7.0 mA |
| CCLK = 80 MHz $V_{DDCore} = 0.8\text{ V}$ | 10 mA |
| CCLK = 110 MHz $V_{DDCore} = 0.8\text{ V}$ | 13 mA |
| CCLK = 144 MHz $V_{DDCore} = 0.9\text{ V}$ | 19 mA |
| CCLK = 180 MHz $V_{DDCore} = 0.9\text{ V}$ | 23 mA |
| CCLK = 204 MHz $V_{DDCore} = 0.9\text{ V}$ | 26 mA |
| CCLK = 240 MHz $V_{DDCore} = 1.0\text{ V}$ | 34 mA |
| CCLK = 270 MHz $V_{DDCore} = 1.0\text{ V}$ | 38 mA |

Table continues on the next page...

Table 2. Core dynamic current (continued)

| Conditions DSP OFF enhanced while (1) code executed from SRAM; Internal LDO disabled | $I_{DDVDDCore}$ |
|---|-----------------|
| CCLK = 300 MHz $V_{DDCore} = 1.13\text{ V}$ | 50 mA |

3.1.3 DSP domain dynamic power

- The DSP sits in its own power island that can be turned on and off.
- The table shows consumption running an FFT.
 - Leakage current is what is present when the DSP is switched on.
 - Dynamic current reflects operating frequency.
- For example, consumption at 0.8 V and 100 MHz:

$$6.79\text{mA} + 10\mu\text{A} = 6.8\text{mA or } 5.44\text{mW}$$

Table 3. DSP dynamic current

| Conditions CM33 WFI FFT code executed from SRAM partition 12; Internal LDO disabled | $I_{DDVDDCore}$ |
|--|-----------------|
| CCLK = 12 MHz $V_{DDCore} = 0.7\text{ V}$ | 4.6 mA |
| CCLK = 48 MHz $V_{DDCore} = 0.7\text{ V}$ | 11 mA |
| CCLK = 60 MHz $V_{DDCore} = 0.7\text{ V}$ | 14 mA |
| CCLK = 80 MHz $V_{DDCore} = 0.8\text{ V}$ | 20 mA |
| CCLK = 110 MHz $V_{DDCore} = 0.8\text{ V}$ | 27 mA |
| CCLK = 144 MHz $V_{DDCore} = 0.8\text{ V}$ | 34 mA |
| CCLK = 180 MHz | 42 mA |

Table continues on the next page...

Table 3. DSP dynamic current (continued)

| Conditions CM33 WFI FFT code executed from SRAM partition 12; Internal LDO disabled | $I_{DDVDDCore}$ |
|--|-----------------|
| $V_{DDCore} = 0.8\text{ V}$ | |
| CCLK = 204 MHz $V_{DDCore} = 0.8\text{ V}$ | 47 mA |
| CCLK = 240 MHz $V_{DDCore} = 0.9\text{ V}$ | 63 mA |
| CCLK = 270 MHz $V_{DDCore} = 0.9\text{ V}$ | 71 mA |
| CCLK = 300 MHz $V_{DDCore} = 0.9\text{ V}$ | 78 mA |
| CCLK = 400 MHz $V_{DDCore} = 1.0\text{ V}$ | 117 mA |
| CCLK = 600 MHz $V_{DDCore} = 1.13\text{ V}$ | 207 mA |

3.2 Sleep

Sleep mode occurs when an interrupt is enabled or when a reset occurs. The device then returns to its original power configuration defined by the contents of the `PDRUNCFG` and `PSCCTL` registers. If a reset occurs, it enters the default configuration in Active mode.

- ↓ Stop the clock to the CPU (system clock).
- ↓ Suspend instruction execution until RESET or an interrupt occurs.
- You can block the Peripherals and continue the operation.
- Peripherals can generate interrupts to resume execution.
- SRAM that was not shut down maintain their content.
- ↑ CPU state and registers and peripheral registers are maintained.
- ↑ Pins logic levels remain static.

3.2.1 Sleep mode power consumption

Table 4. Core power consumption in Sleep mode

| Conditions DSP OFF enhanced while (1) code executed from SRAM; Internal LDO disabled | $I_{DDVDDCore}$ |
|---|-----------------|
| CCLK = 12 MHz $V_{DDCore} = 0.7\text{ V}$ | 3.0 mA |
| CCLK = 48 MHz $V_{DDCore} = 0.7\text{ V}$ | 4.0 mA |
| CCLK = 250 MHz $V_{DDCore} = 1.0\text{ V}$ | 20.3 mA |

3.3 Deep Sleep

The Deep Sleep mode is configurable and can potentially turn off nearly all on-chip power consumption other than the on-chip power supply, with the cost of a longer wake-up time.

- ↓ Stop clock to the CPU (system clock).
- ↓ Power consumed by analog peripherals, dynamic power used by the processor.
- Peripherals, if not configured, receive no internal clocks.
- GPIO Pin Interrupts, and selected peripherals can be left running.
- SRAM that was not shut down maintain their content.
- Analog blocks are powered down by default but can be software-configured.
- ↑ CPU state and registers and peripheral registers are maintained.
- ↑ Pins logic levels remain static.

Before going into Deep Sleep, ensure that:

1. Active mode $V_{DDCORE} \geq LVDCORECTRL.LVDCORELVL + 20\text{ mV}$.
2. Deep Sleep mode $V_{DDCORE} < LVDCORECTRL.LVDCORELVL$.

If it is not done, your application hangs and never fully wakes up. It is because when using an external PMIC, on initial power-up and on wake-up from Deep Sleep, the PMC logic uses the LVD status to determine when V_{DDCORE} is high enough to allow the MCU to operate. There is no other handshake with the PMIC to indicate to the PMC that V_{DDCORE} is OK for operation. For example, when the LVD trip is set to the minimum (0.72 V) and the application is using an external PMIC, the V_{DDCORE} must drop below 0.72 V in the Deep Sleep mode and rise above 0.74 V when waking up (it is 0.72 V + 20 mV hysteresis).

3.3.1 Deep Sleep power consumption

- Current Consumption
 - Core leakage + memory leakage
 - With 5 MBytes, retained leakage on current samples is between 80-90uA @ 0.6 V.
 - With 32 KB, retained leakage on current samples is between 40-50uA @ 0.6 V.
 - Total leakage power is between 48-54uW

- Memories are 6uW/Mbyte
- Pad leakage
 - Pads can be power switched to turn off leakage

Table 5. Voltage domain dynamic current

| Pad segment | Conditions All power supplies = 1.8 V, except USB1_VDD3V3 = 3.3 V | Current consumption |
|------------------|---|---------------------|
| I_{VDD1V8} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 109 μ A |
| I_{VDD1V8_1} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 65 μ A |
| $I_{VDDCORE}$ | SRAM (32 KB) powered, Internal LDO disabled. Array On, Periphery Off | 75 μ A |
| $I_{VDDCORE}$ | SRAM (128 KB) powered, Internal LDO disabled. Array On, Periphery Off | 77 μ A |
| $I_{VDDCORE}$ | SRAM (4.5 MB) powered, Internal LDO disabled. Array On, Periphery Off | 190 mA |
| I_{VDD_AO1V8} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 0.6 μ A |
| I_{VDDIO_0} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 7.0 μ A |
| I_{VDDIO_1} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 0.9 μ A |
| I_{VDDIO_2} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 6.4 μ A |
| I_{VDDA_1V8} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 0.1 μ A |
| I_{VDDA_BIAS} | SRAM (128 KB) powered, | 0.1 μ A |

Table continues on the next page...

Table 5. Voltage domain dynamic current (continued)

| Pad segment | Conditions All power supplies = 1.8 V, except USB1_VDD3V3 = 3.3 V | Current consumption |
|--------------------|--|---------------------|
| | Internal LDO enabled. Array On, Periphery Off | |
| I_{VREFP} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 0.1 μ A |
| I_{USB1_VDD3V3} | SRAM (128 KB) powered, Internal LDO enabled. Array On, Periphery Off | 0.1 μ A |

3.4 Deep Power-down

Wake-up from Deep Power-Down is done through RESET or RTC.

- ↓ Shut OFF the entire chip clock and power.
- ↓ SRAM and register content are not retained.
- ↓ All functional pins are tri-stated as long as supplied externally.
- ↑ External supplies are powered ON.
- ↑ V_{DD_AO1V8} is ON, then RTC is ON.

3.4.1 Optimizing power in the Deep Power-down mode

The Deep Power-Down mode has no configuration options. All clocks, the core, and all peripherals are powered down. Only the RTC is powered, as long as power is supplied to the V_{DD_AO1V8} pin.

3.4.2 Deep Power-down power consumption

- $V_{DDCORE} < 1 \mu A$
- Ports with high-speed pads must be turned off externally.
 - V_{DDIO_0} - V_{DDIO_2} & V_{DDIO_4}
 - If ports are off, the pads are fail-safe.
- V_{DDIO_3} does not have high-speed pads.
 - Leakage current is less than 50 nA.
- Total deep power down current is $< 1.5 \mu A$ if V_{DDIO_1} , V_{DDIO_2} , and V_{DDIO_4} are load switched.

3.5 Full Deep Power-down

External power must be restored prior to wake-up. Wake-up from full Deep Power-down is done through RESET or RTC.

- ↓ Shut OFF the entire chip clock and power.
- ↓ SRAM and register content are not retained.
- ↓ All functional pins are tri-stated as long as supplied externally.

↓ External supplies are powered OFF.

↑ V_{DD_AO1V8} is ON then RTC is ON.

3.5.1 Full Deep Power-down power consumption

Table 6. Core power consumption in full Deep Power-down

| Pad segment | Conditions | Current consumption |
|------------------------|---|---------------------|
| I _{VDD_AO1V8} | All power supplies = 1.8 V, except USB1_VDD3V3 = 3.3 V | |
| | LDO disabled. RTC Off | 0.6 uA |

3.6 Power mode transitions

Transitions from active mode to various low-power modes are initiated by software and wakeups are triggered by hardware events (resets or interrupts previously configured by software). Entering Deep Sleep or Deep Power-down modes is initiated by first configuring PDSLEEPCFG to select off/on/low power mode for various blocks and then executing the ARM WFI command in the M33 core. Wake-up from any sleep or Power-down mode is triggered by an active wake-up source or reset or POR. It is summarized in the figure below:

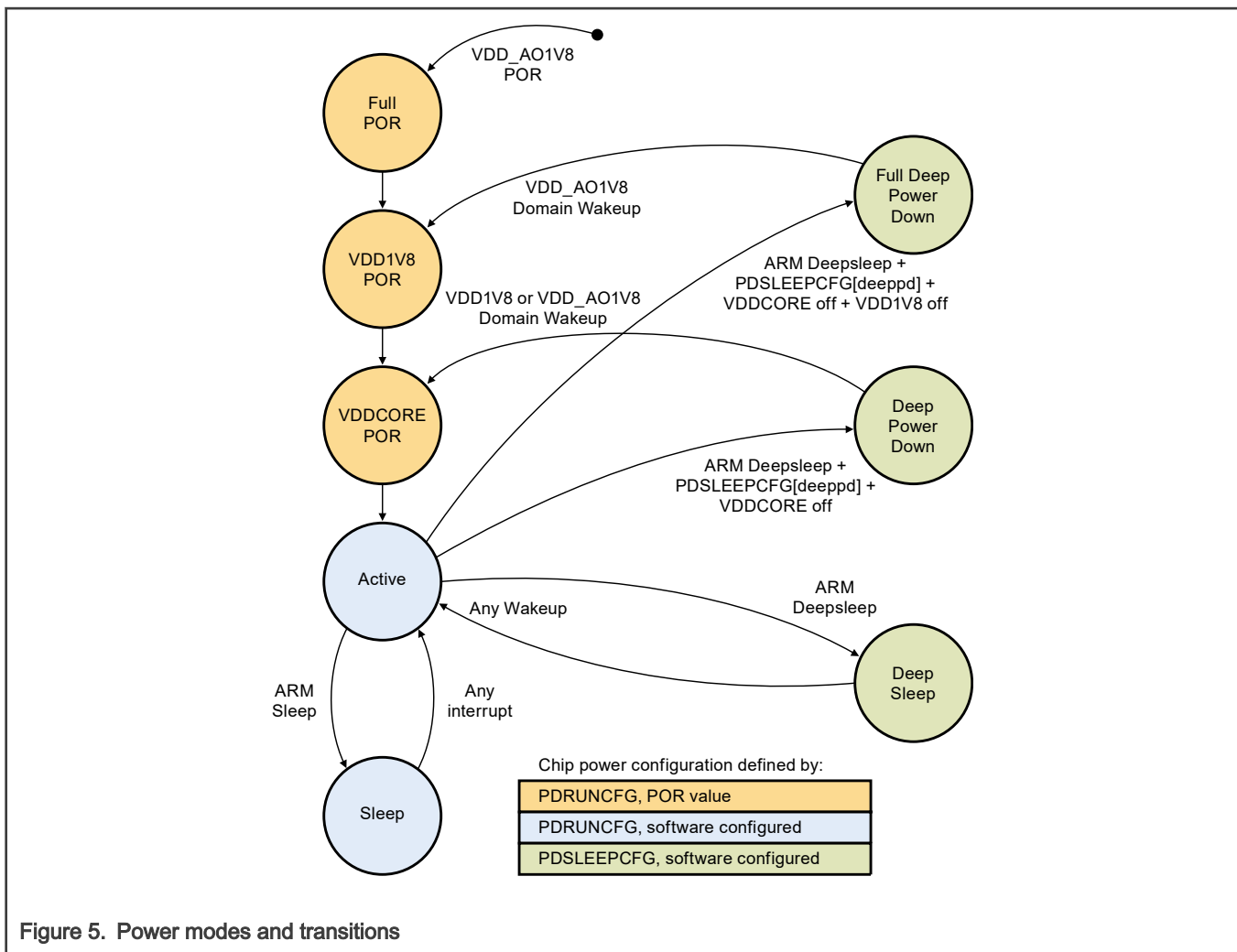


Figure 5. Power modes and transitions

4 Pad Group currents

RT600 has 3 pad groups, `VDDIO_0`–`VDDIO_2`. Each pad group has a separate rail so they can all be powered by different voltage levels ranging from 1.71 V to 3.6 V.

4.1 Pad Group GPIOs

The following [table](#) shows GPIOs belonging to the specific pad group.

Table 7. GPIO pins associated to the pad group

| Pin | GPIO Pins |
|---------|--|
| VDDIO_0 | PIO0_0 to PIO0_13 PIO1_11 to PIO1_29 PIO2_12 to PIO2_23 PIO3_25 to PIO3_31 PIO4_0 to PIO4_10 PIO7_24 to PIO7_31 |
| VDDIO_1 | PIO0_14 to PIO0_31 PIO1_0 to PIO1_10 PIO2_24 to PIO2_31 PIO3_0 to PIO3_24 PMIC_I2C_SCL PMIC_I2C_SDA |
| VDDIO_2 | PIO1_30 to PIO1_31 PIO2_0 to PIO2_11 |

Depending on what voltage is applied to the `VDDIO_x` rail, the appropriate range setting must be configured in the `PADVRANGE` register shown in [Table 8](#)

Table 8. PADVRANGE – PMC GPIO VDDIO Range Selection Control

| VDDIO_xRANGE | Description | Reset Value |
|--------------|---|-------------|
| 00 | Voltage from 1.71 V to 3.6 V (wide voltage range). Consumes static current to detect the <code>VDDIO0</code> level. It is recommended to change this value to 01 to reduce power consumption. | 0x0 |
| 01 | Voltage from 1.71 V to 1.98 V (low-voltage range), <code>VDDIO</code> detector off. | |
| 10 | Voltage from 3.0 V to 3.6 V (high-voltage range), <code>VDDIO</code> detector off. | |
| 11 | Reserved | - |

5 Clock gating

RT600 supports the ability to clock-gate various AHB peripherals and SRAMs. It can be accomplished in two ways: automatic and manual clock gating.

5.1 Automatic clock gating

Automatic clock gating turns off the bus clock to the related function if it is not accessed for 16 clocks. A subsequent access incurs a one clock delay for the clock gate to be turned on.

The following registers automatically control clock gating:

Table 9. Control gating peripherals

| Auto clock gating register | Selected functions |
|------------------------------|--|
| SYSCTL0_AUTOCLKGATEOVERRIDE0 | AHB2APB0 AHB2APB1 CRC_ENGINE CASPER DMAC0 DMAC1 |
| SYSCTL0_AUTOCLKGATEOVERRIDE1 | SRAMIF0 - SRAMIF29 |
| SYSCTL0_CLKGATEOVERRIDE0 | SDIO_0 SDIO_1 USBHSPHY ADC MU ACMP PMC |

While the primary purpose of these registers is to block access to a particular commander, an alternate effect is to prevent the associated clock from being propagated. It can result in a significant reduction in power in the case where a partition is not being used.

6 Code locality

The use of the different SRAM partitions results in different current consumption. It is due to the physical location of the various partitions on the chip. For example, the following list outlines the current draw from lowest to highest SRAM partition running an advance-while 1, Typical, 25C, NBB, 198 MHz (FRO), all memories ON (only one partition clocked):

Table 10. Current draw from lowest to highest SRAM partition

| Partition # | IVDDCORE | Size (KB) |
|-------------|----------|-----------|
| 2 | 26.6 | 32 |

Table continues on the next page...

Table 10. Current draw from lowest to highest SRAM partition (continued)

| Partition # | IVDDCORE | Size (KB) |
|-------------|----------|-----------|
| 3 | 27.1 | 32 |
| 4 | 27.6 | 32 |
| 5 | 27.5 | 32 |
| 6 | 27.1 | 32 |
| 7 | 26.9 | 32 |
| 8 | 30.0 | 64 |
| 9 | 28.8 | 64 |
| 10 | 30.7 | 64 |
| 11 | 30.1 | 64 |
| 12 | 36.2 | 128 |
| 13 | 34.9 | 128 |
| 14 | 34.3 | 128 |
| 15 | 33.4 | 128 |
| 16 | 26.6 | 256 |
| 17 | 25.8 | 256 |
| 18 | 26.7 | 256 |
| 19 | 25.4 | 256 |
| 20 | 27.5 | 256 |
| 21 | 27.0 | 256 |
| 22 | 29.1 | 256 |
| 23 | 27.4 | 256 |
| 24 | 27.0 | 256 |
| 25 | 27.9 | 256 |
| 26 | 27.8 | 256 |
| 27 | 27.1 | 256 |

Table continues on the next page...

Table 10. Current draw from lowest to highest SRAM partition (continued)

| Partition # | IVDDCORE | Size (KB) |
|-------------|----------|-----------|
| 28 | 26.7 | 256 |
| 29 | 27.5 | 256 |

7 Body bias

RT600 offers three different body bias modes for greater power optimization flexibility: No Body Bias (NBB), Reverse Body Bias (RBB), and Forward Body Bias (FBB). The table below describes when to use each mode and how to enable them.

Table 11. Body bias modes

| Mode | When to use | Bits to consider ² | How to enable using Power Library |
|---|---|--|-----------------------------------|
| NBB | Very low frequencies (for example, <60 MHz @ 0.7 V) | PDRUNCFG [RBB_PD] = 1 PDRUNCFG [FBB_PD] = 1 PDRUNCFG [MAINCLK_SHUTOFF] = 1 | Power_EnterNBB |
| RBB | Only in Deep Sleep mode | PDRUNCFG [RBB_PD] = 0 PDRUNCFG [FBB_PD] = 1 PDRUNCFG [MAINCLK_SHUTOFF] = 1 | Power_EnterRBB |
| FBB ¹ | All other use cases | PDRUNCFG [RBB_PD] = 1 PDRUNCFG [FBB_PD] = 0 PDRUNCFG [MAINCLK_SHUTOFF] = 1 | Power_EnterFBB |
| 1. Default mode 2. There is a specific process that must be followed when switching between body bias modes, which is why we recommend only using the power library API to switch modes. | | | |

If the OTP is not powered down in PDRUNCFG/PDSLEEPCFG, the default setting leaves it in Standby mode, which consumes about 600 uA on VDDCORE, and 2.1 mA on vdd_fuse18 in typical conditions.

8 Fuse block current consumption

The fuse block is used for security, trimming, and user configuration options. The fuse block also referred to as the OTP block has two distinct parts as shown in the figure below: one is where the fuse cells reside and the other is the control and access logic for the fuse bits. The fuse cell part contains analog circuits for programming and reading the cells. The RT600 design added a switch to turn off the analog part of the fuse block.

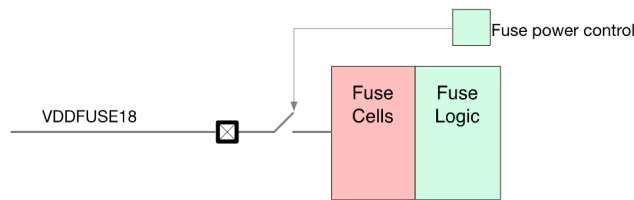


Figure 6. Fuse block

9 RTC current consumption

Independent power island.

Two power pins are as shown in the figure below.

- VDD_AO18 supplies crystal and logic:
 - Logic consumption: 600-700nA.
 - Crystal: 200 nA.
 - Total RTC current 800-900nA.
- VDDEAO supplies the pads:
 - Leakage current is less than 50 nA.

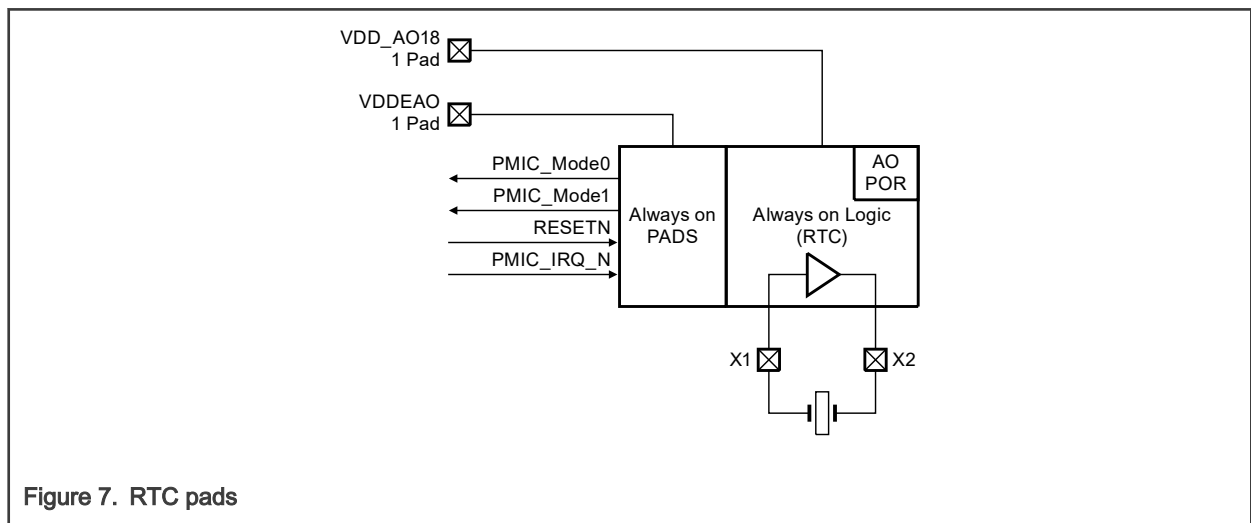


Figure 7. RTC pads

10 Optimization techniques

This section is dedicated to optimization techniques in different modes.

10.1 Optimizing power in Active mode

To minimize power consumption in Active mode, do the following:

1. Power down unused blocks via the `PDRUNCFG0/1/2/3` registers. Power Down (PD) bits and other power controls include:
 - PD bits for all Analog blocks (incl oscillators, PHYs, and so on)
 - SRAM array and periphery power switches

- Disable array and periphery of unused SRAM partitions.
 - Set the correct PMIC mode pins (depending on how the PMIC was configured) if using an external PMIC.
 - The power library uses mode 00 for Active mode, configure the PMIC accordingly.
 - VDDCORE high-power / low-power mode control
 - Set the correct body bias mode according to [Table 7](#).
 - These bits are automatically configured by the power library according to the power mode, try not to modify these bits.
 - Refer to the [Body bias](#) section for more information.
 - PLL enables (analog and digital)
 - HS pad controls
 - DSP, OTP, and ROM power-off switches.
 - When the OTP bit is powered off, the `OTPSWREN` bit in the PMC CTRL register must also be set. If the RT600 power library is used, it is done automatically.
 - Software must not set the `MAINCLK_SHUTDOWN` bit in `PDRUNCFG0`; otherwise, the clocks cannot be turned back on because software cannot run without clocks and the wake-up sources are not enabled because the chip is still in Active mode.
 - When the chip is running and the VDDCORE regulator is in HP mode (`VDDCOREREG_LP=0`), putting the LVD and PORs into LP mode (`PORCORE_LP=1` and `LVDCORE_LP=1`) only saves about 14 uA.
2. Disable individual bus clocks for peripherals and memories via the `PSCCTL0/1/2` registers.
 - These bus clocks are typically used when writing to or reading from each peripheral's register space. Clocks must be turned off when the peripheral is not in use. Some of them must be turned off after the peripheral is initialized (for example, IOCON)
 3. Set the power mode for the Xtal Oscillator. It is recommended that the High-gain mode is used in high-noise environments or with jitter sensitive applications; otherwise, use low-power mode.
 4. If the 32 kHz oscillator is not being used, make sure to disable it by clearing bit 0 (`ENA32KHZ`) in `OSC32KHZCTL0` and setting bit 8 (`RTC_OSC_PD`) in `RTC CTRL`.
 - Both `ENA32KHZ` and `RTC_OSC_PD` must be configured to enable/disable the 32 kHz Oscillator.
 5. Disable any unused PFD outputs via the `SYSPLLOPFD` register.
 - Bits [5:0], [13:8], [21:16] and [29:24] establish the PFD output frequencies for PFD0,1,2,3 respectively (For a given VCO base frequency). Bits 7, 15, 23 and 31 gate off the corresponding PFD outputs entirely.
 6. Select input 7 for unused peripherals for all the various functional clock muxes (`xxxCLKSEL` Registers) in `CLKCTL`.
 - Selecting input 7 shuts off the clock tree entirely to that peripheral.

10.2 Optimizing power in Sleep mode

Refer to the [Optimizing power in Active mode](#) section.

10.3 Optimizing power in Deep Sleep mode

Power consumption in Deep Sleep mode is primarily determined by enabled analog wake-up sources. Serial peripherals and pin interrupts configured to wake up the contribute to the power consumption only to the extent that they are clocked by external sources. All wake-up events (other than reset) must be enabled in the NVIC. In addition, any related analog block (for example, the RTC oscillator or the watchdog oscillator) must be explicitly enabled in the call to the power API function.

1. Power down unused blocks in Deep Sleep via the `PDSLEEPCFG0/1/2/3` registers. Power Down (PD) bits and other power controls include:

- Disable all SRAM peripheral (PDSLEEPCFG3) and only keep the SRAM array enabled (PDSLEEPCFG2) for the SRAM partitions you wish to retain.
 - Set the MAINCLK_SHUTOFF bit in PDSLEEPCFG0 if main_clk is left enabled in Deep Sleep mode.
 - For faster wake-up time, the FRO can be left enabled in Deep Sleep mode. In that case, there is a MAINCLK_SHUTOFF bit in the PDRUNCFG0. With that set, the main_clk is gated off when the MCU enters Deep Sleep mode, and most of the FRO clock tree is not active.
 - Set the correct PMIC mode pins (depending on how the PMIC was configured) if using external PMIC.
 - The power library uses mode 01 for Deep Sleep mode, configure PMIC accordingly.
 - VDDCORE LP/HP control
 - The VDDCORE regulator must be put into LP mode during Deep Sleep mode when there is little to no activity in the chip.
 - Set the Body Bias mode to RBB.
 - These bits are automatically configured by POWER_EnterDeepSleep API.
 - Refer to the [Body bias](#) section for more information.
 - PLL enables (analog and digital)
 - HS pad controls
 - DSP, OTP, and ROM power-off switches.
 - When the OTP bit is powered off, the OTPSWREN bit in the PMC CTRL register must also be set. If the RT600 power library is used, it is done automatically.
 - In Deep Sleep mode, with all the PMU in LP mode it makes sense to put the monitors into LP mode (PORCORE_LP and LVDCORE_LP).
2. See items 2-7 in the [Optimizing power in Active mode](#) section.

10.4 Optimizing power in Full Deep Power-down mode

Full Deep Power-down mode has no configuration options.

11 References

1. i.MX RT6xx User manual (document: [UM11159](#))
2. [i.MX RT600 Rev B0 Data Sheet](#)
3. AN12094-Power consumption and measurement (document: [AN12094](#))
4. AN12844-Power consumption and measurement of i.MX RT6xx DSP (document: [AN12844](#))

12 Revision history

Table 12. Revision history

| Revision number | Date | Substantive changes |
|-----------------|------------------|--|
| 1 | 07 April 2022 | <ul style="list-style-type: none"> • Updated VDD_Core • Updated Table 10 |
| 0 | 14 December 2021 | Initial release |

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